



N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY

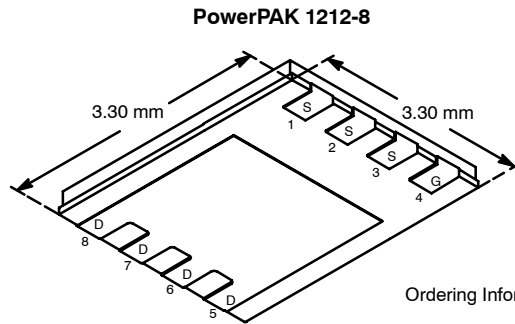
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
200	0.240 @ $V_{GS} = 10$ V	2.6
	0.250 @ $V_{GS} = 6$ V	2.5

FEATURES

- PWM-Optimized TrenchFET® Power MOSFET
- 100% R_g Tested
- Avalanche Tested

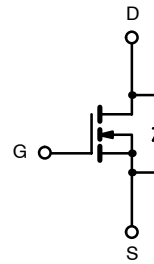
APPLICATIONS

- Primary Side Switch
 - Telecom Power Supplies
 - Distributed Power Architectures
 - Miniature Power Modules



Bottom View

Ordering Information: Si7820DN-T1—E3



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	200		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	2.6	1.7	A
	T _A = 70°C		2.1	1.3	
Pulsed Drain Current		I _{DM}	10		
Continuous Source Current (Diode Conduction) ^a		I _S	3.2	1.3	
Single Avalanche Current	L = 0.1 mH	I _{AS}	3.5		mJ
Single Avalanche Energy		E _{AS}	0.6		
Maximum Power Dissipation ^a	T _A = 25°C	P _D	3.8	1.5	W
	T _A = 70°C		2.0	0.8	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	26	33	$^\circ\text{C/W}$
	Steady State		65	81	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.9	2.4	

Notes

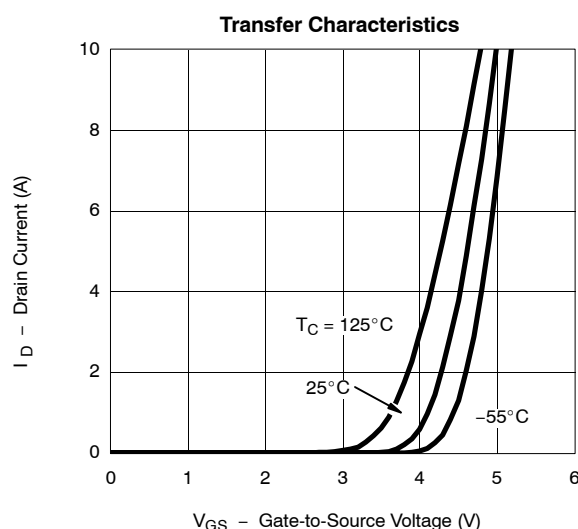
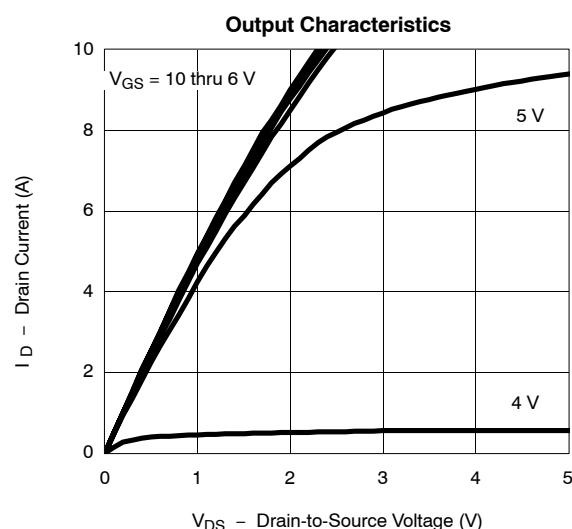
a. Surface Mounted on 1" x 1" FR4 Board.

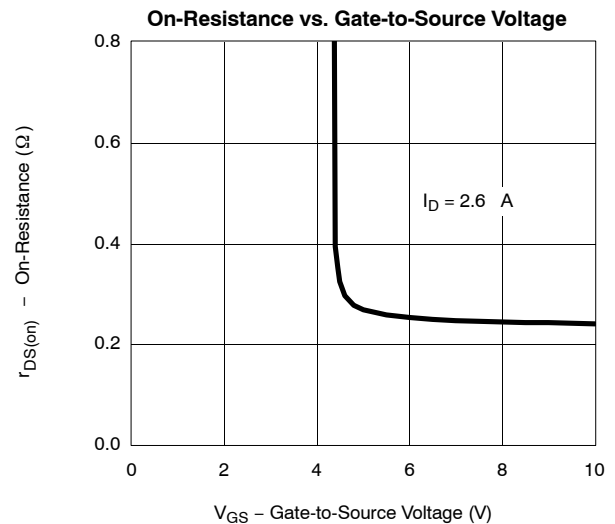
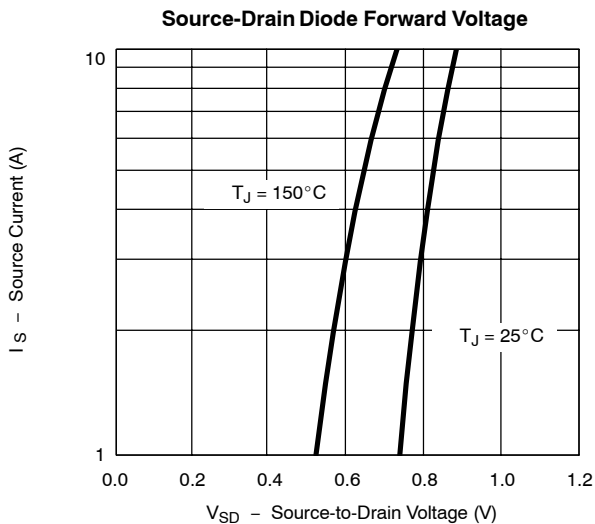
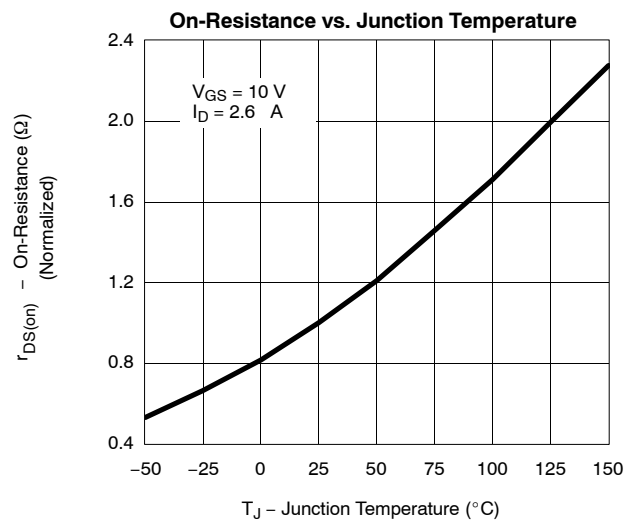
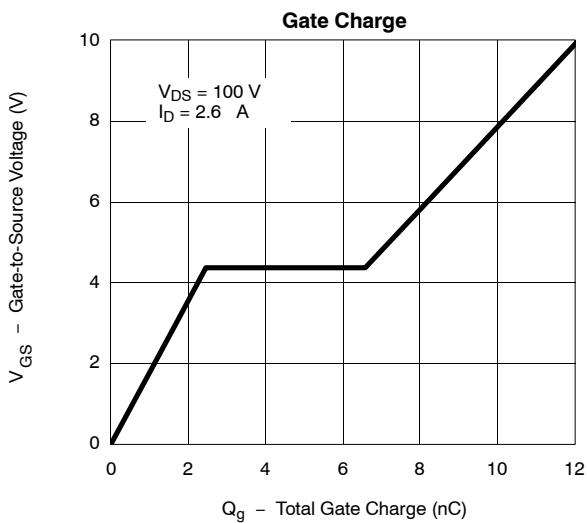
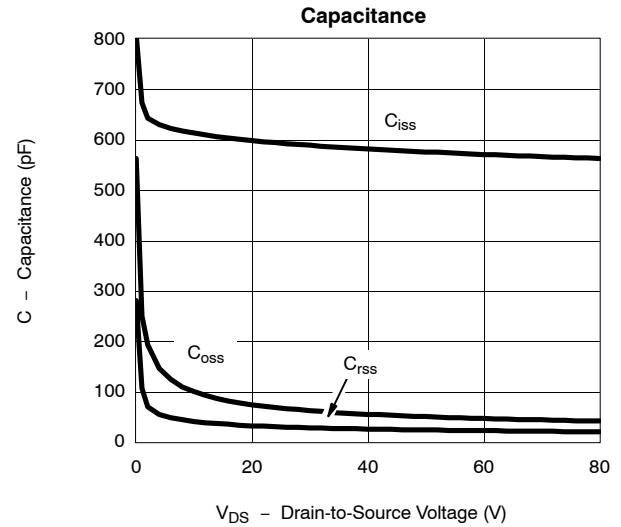
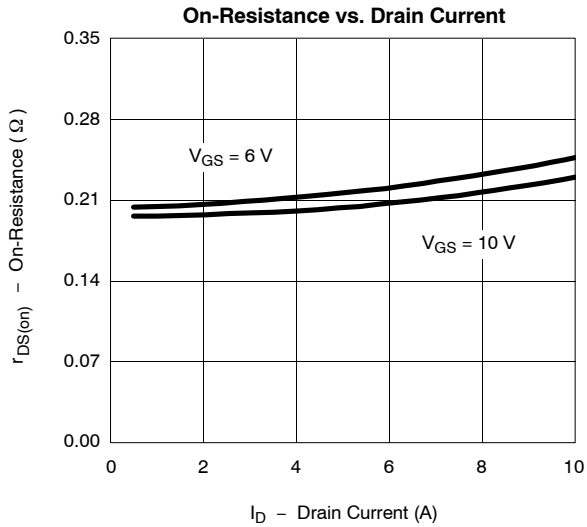
MOSFET SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

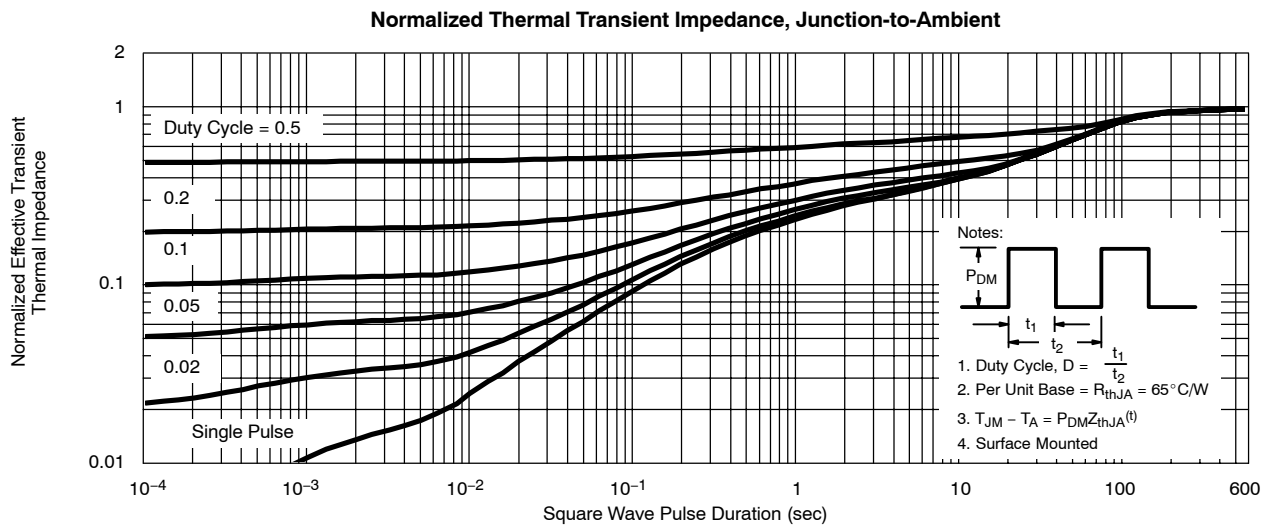
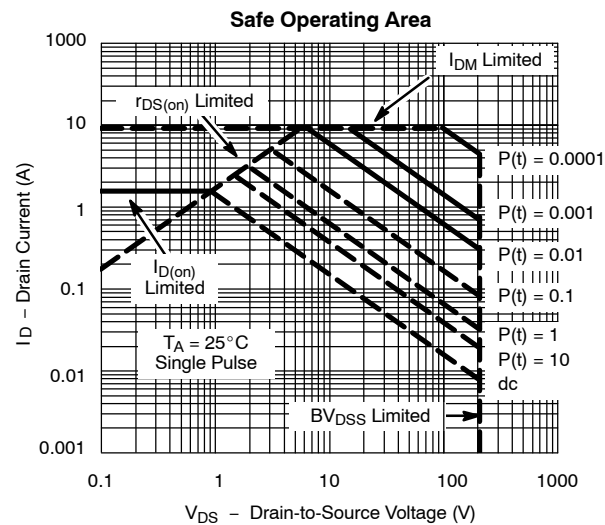
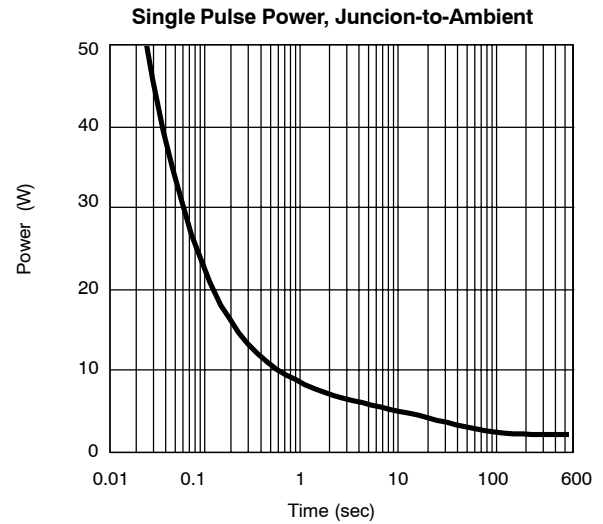
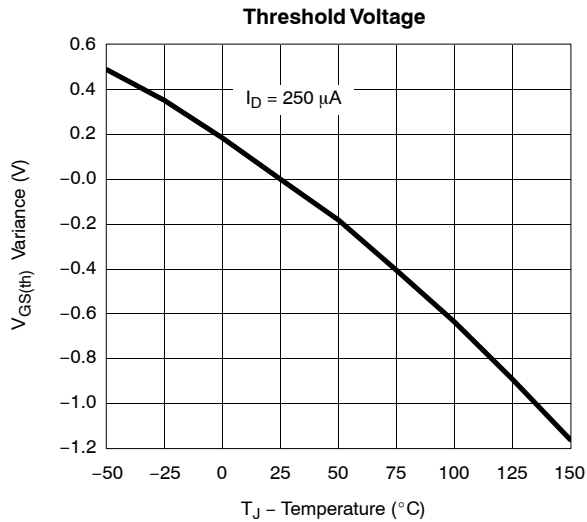
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	2		4	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 200\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 200\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	10			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 2.6\ \text{A}$		0.200	0.240	Ω
		$V_{GS} = 6\ \text{V}$, $I_D = 2.5\ \text{A}$		0.210	0.250	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 2.6\ \text{A}$		8		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 3.2\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.78	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 100\ \text{V}$, $V_{GS} = 10\ \text{V}$, $I_D = 2.6\ \text{A}$		12.1	18	nC
Gate-Source Charge	Q_{gs}			2.5		
Gate-Drain Charge	Q_{gd}			4.1		
Gate Resistance	R_g	$f = 1\ \text{MHz}$	1	2.3	3.9	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\ \text{V}$, $R_L = 100\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_G = 6\ \Omega$		11	20	ns
Rise Time	t_r			12	20	
Turn-Off Delay Time	$t_{d(off)}$			30	45	
Fall Time	t_f			17	30	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 3.2\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		65	100	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

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